

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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Attorney Docket Number

2269-4218US (99-0796.00/US)

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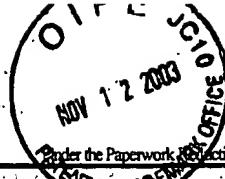
FOREIGN PATENT DOCUMENTS

Examiner Signature	HUNG VU	Date Considered	04/19/04
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Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Complete if Known

Application Number	09/651,620
Filing Date	August 30, 2000
First Named Inventor	Eugene P. Marsh
Group Art Unit	2811
Examiner Name	H. Vu
Attorney Docket Number	2269-4218US (99-0796.00/US)

U.S. PATENT DOCUMENTS					
Examiner Initials *	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
Vin		US-4,250,210	02/1981	Crosby et al.	—
		US- 4,982,309	01/1991	Shepherd	
		US- 5,080,862	01/1992	Luthra	
		US- 5,126,016	06/1992	Glennning et al.	1C
		US- 5,130,172	07/1992	Hicks et al.	2300
		US- 5,241,137	08/1993	Kiribayashi	4/11
		US- 5,288,675	02/1994	Chen et al.	200
		US- 5,314,727	05/1994	McCormick et al.	200
		US- 5,352,488	10/1994	Spencer et al.	200
		US- 5,525,181	06/1996	Bruckner et al.	200
		US- 5,529,953	06/1996	Shoda	200
		US- 5,614,795	03/1997	Kim	200
		US- 5,618,761	04/1997	Eguchi et al.	200
		US- 5,662,815	09/1997	Kim	200
		US- 5,705,442	01/1998	Yen et al.	200
		US- 5,729,054	03/1998	Summerfelt et al.	200
		US- 5,742,322	04/1998	Cranton et al.	200
		US- 5,874,174	02/1999	Okuda et al.	200
		US- 5,885,750	03/1999	Hsiao et al.	200
		US- 5,994,034	11/1999	Maehtata	200
Vin		US- 6,197,628 B1	03/2001	Vaatstra et al.	—

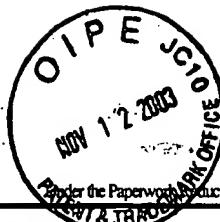
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Application Number	09/651,620
Filing Date	August 30, 2000
First Named Inventor	Eugene P. Marsh
Group Art Unit	2811
Examiner Name	H. Vu

Attorney Docket Number 2269-42181US (99-0796.00/US)

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OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
<u>HV</u>		Cowles et al., Chemical Communications, p. 392, 1969.	
		Green et al., "Chemical Vapor Deposition of Ruthenium and Ruthenium Dioxide Films", J. Electrochem. Soc., Vol. 132, No. 11, pp. 2677-2685, Nov. 1985.	
		Simpson et al., "Atomic Layer Epitaxy," Chem Br., Vol. 23, No. 1, pp. 37-38, 40, Jan. 1987.	
		Hirva et al., "Theoretical Studies on the Growth Mechanisms of Silicon Thin Films by Atomic Layer Epitaxy," Surface Science, 220, pp. 137-151, 1989.	
		Gregory et al., "Conditions for the Deposition of CdTe by Electrochemical Atomic Layer Epitaxy," J. Electrochem. Soc., Vol. 138, No. 5, pp. 1279-1284, May 1991.	
		Koleske et al., "Growth of Si on (100) via H/Cl Exchange and the Effect of Interfacial Boron," J. Appl. Phys., Vol. 72, No. 9, pp. 4073-4082, 1 Nov. 1992.	
		Norton et al., "Organometallic Chemical Vapour Deposition of Platinum and Gold: Heterogeneous Deposition and Surface Chemistry," Surface Science, 307-309, pp. 172-176, 1994.	
		Borup et al., "Electrochemical and Vacuum Behavior of Carbon Monoxide and Lead Coadsorbed on Platinum (111)," J. Electroanalytical Chem., Vol. 374, pp. 235-244, 1994.	
		Aquino et al., "Evidence for a Surface Methylene Species in the Decomposition of Trimethylgallium on GaAs(100)-(4x1): A High Resolution Electron Energy Loss Spectroscopy Study," Surface Science, Vol. 327, pp. 74-80, 1995.	
		Vilammi, "Monolayer Thickness in Atomic Layer Deposition," Thin Solid Films, Vol. 279, pp. 124-130, 1996.	
		George et al., "Surface Chemistry for Atomic Layer Growth," J. Phys. Chem., Vol. 100, pp. 13121-13131, 1996.	
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		Silmon et al., "Thickness Profiles of Thin Films Caused by Secondary Reactions in Flow-Type Atomic Layer Deposition Reactors," J. Phys. D: Appl. Phys., Vol. 30, pp. 1725-1728, 1997.	
<u>HV</u>		Min et al., "Atomic Layer Deposition of TiN Films by Alternate Supply of Tetrakis (ethylmethylamino)-Titanium and Ammonia," Jpn. J. Appl. Phys., Vol. 37, pp. 4999-5004, 1998.	

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